This international standard was developed in accordance with internationally recognized principles on standardization established in the Decision on Principles for the Development of International Standards, Guides and Recommendations issued by the World Trade Organization Technical Barriers to Trade (TBT) Committee.



Designation: E2444 – 11 (Reapproved 2018)

Standard Terminology Relating to Measurements Taken on Thin, Reflecting Films¹

This standard is issued under the fixed designation E2444; the number immediately following the designation indicates the year of original adoption or, in the case of revision, the year of last revision. A number in parentheses indicates the year of last reapproval. A superscript epsilon (ε) indicates an editorial change since the last revision or reapproval.

1. Scope

1.1 This standard consists of terms and definitions pertaining to measurements taken on thin, reflecting films, such as found in microelectromechanical systems (MEMS) materials. In particular, the terms are related to the standards in Section 2, which were generated by Committee E08 on Fatigue and Fracture. Terminology E1823 Relating to Fatigue and Fracture Testing is applicable to this standard.

1.2 The terms are listed in alphabetical order.

1.3 This international standard was developed in accordance with internationally recognized principles on standardization established in the Decision on Principles for the Development of International Standards, Guides and Recommendations issued by the World Trade Organization Technical Barriers to Trade (TBT) Committee.

2. Referenced Documents

2.1 ASTM Standards:²

E1823 Terminology Relating to Fatigue and Fracture TestingE2244 Test Method for In-Plane Length Measurements ofThin, Reflecting Films Using an Optical InterferometerE2245 Test Method for Residual Strain Measurements of

Thin, Reflecting Films Using an Optical Interferometer E2246 Test Method for Strain Gradient Measurements of Thin, Reflecting Films Using an Optical Interferometer

3. Terminology

3.1 Terms and Their Definitions:

2-D data trace—a two-dimensional group of points that is extracted from a topographical 3-D data set and that is parallel to the *xz*- or *yz*-plane of the interferometric microscope. **E2244, E2245**

- **3-D data set**—a three-dimensional group of points with a topographical *z*-value for each (x, y) pixel location within the interferometric microscope's field of view. **E2244**, **E2245**, **E2246**
- anchor—in a surface-micromachining process, the portion of the test structure where a structural layer is intentionally attached to its underlying layer.
 E2244, E2245, E2246
- **anchor lip**—in a surface-micromachining process, the freestanding extension of the structural layer of interest around the edges of the anchor to its underlying layer.
 - DISCUSSION—In some processes, the width of the anchor lip may be zero. **E2244, E2245, E2246**
- bulk micromachining—a MEMS fabrication process where the substrate is removed at specified locations. E2244, E2245, E2246
- cantilever—a test structure that consists of a freestanding beam that is fixed at one end. E2244, E2245, E2246
- fixed-fixed beam —a test structure that consists of a freestanding beam that is fixed at both ends. E2244, E2245

in-plane length (or deflection) measurement, *L* (or *D*) [L]—the experimental determination of the straight-line distance between two transitional edges in a MEMS device. DISCUSSION—This length (or deflection) measurement is made parallel to the underlying layer (or the *xy*-plane of the interferometric microscope). E2244, E2245, E2246

interferometer—a non-contact optical instrument used to obtain topographical 3-D data sets.

DISCUSSION—The height of the sample is measured along the z-axis of the interferometer. The x-axis is typically aligned parallel or perpendicular to the transitional edges to be measured. E2245, E2246

MEMS—microelectromechanical systems. E2244, E2245, E2246

microelectromechanical systems, MEMS—in general, this term is used to describe micron-scale structures, sensors, actuators, and technologies used for their manufacture (such as, silicon process technologies), or combinations thereof. E2244, E2245, E2246

residual strain, ε_r —in a MEMS process, the amount of deformation (or displacement) per unit length constrained

¹ This test method is under the jurisdiction of ASTM Committee E08 on Fatigue and Fracture and is the direct responsibility of Subcommittee E08.02 on Standards and Terminology.

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² For referenced ASTM standards, visit the ASTM website, www.astm.org, or contact ASTM Customer Service at service@astm.org. For *Annual Book of ASTM Standards* volume information, refer to the standard's Document Summary page on the ASTM website.